

0805566-062901

5100

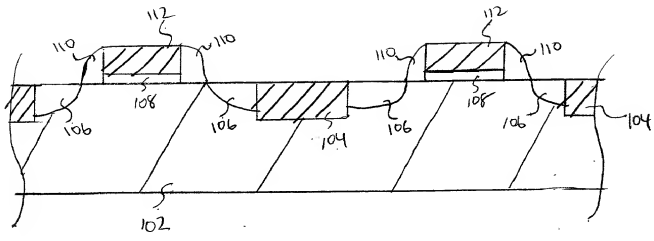


FIG. 1A

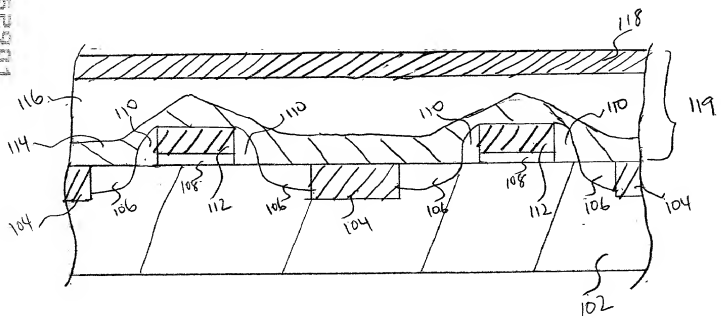


FIG. 1B

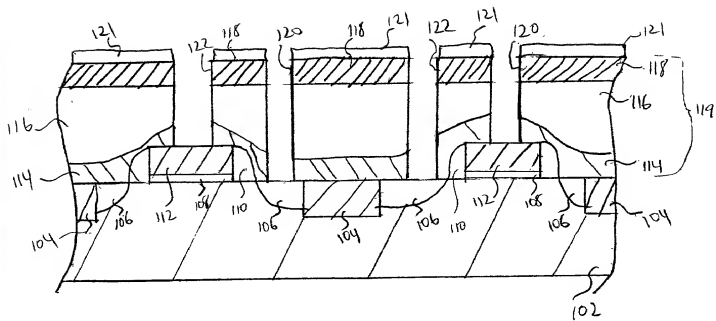


FIG 1C

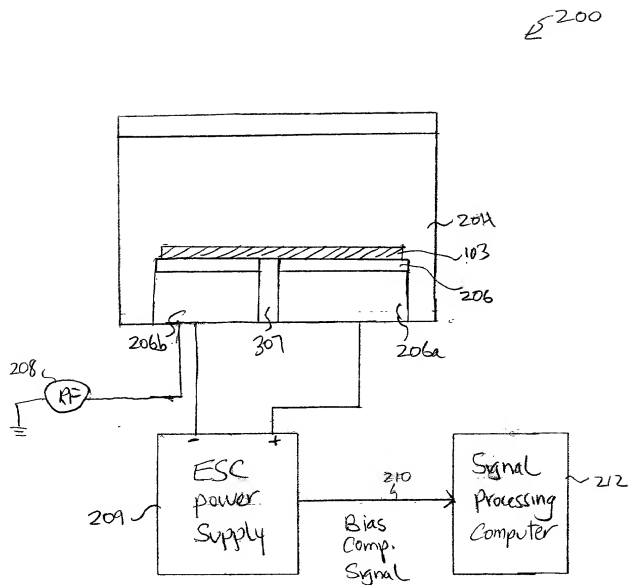


FIG. 2

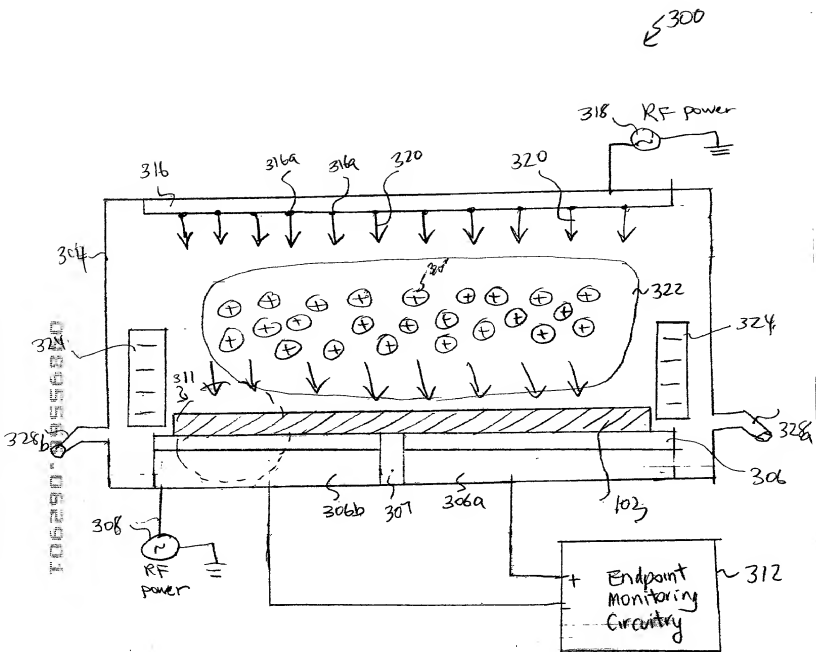


FIG. 3A

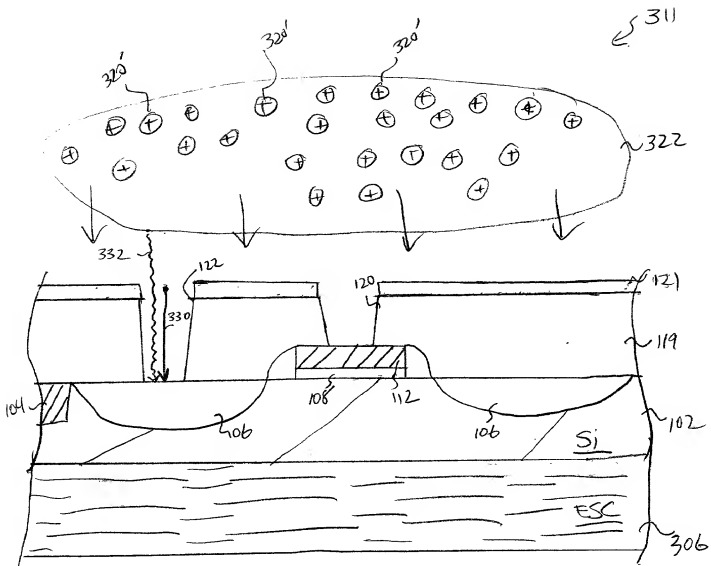


FIG. 3B

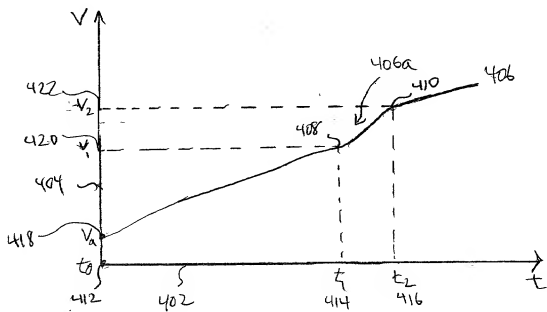


FIG. 4

start

500

Provide a substrate having
an ILD layer to be etched

502

Inserting substrate into
a chamber

504

Introducing etchant gases

506

Powering up the chamber
to strike a plasma to
commence etching

508

Monitoring a substrate
bias level

510

Discontinue the etching
when a target bias compensation
level is reached

512

Removing substrate from
chamber and prepare for
additional processing if
desired

514

Done

FIG. 5A

0986-6708

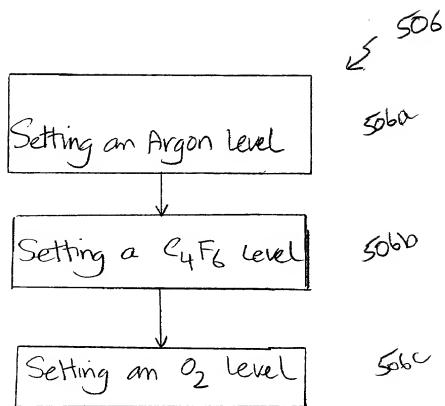


FIG. 5B

09895566-062901

508

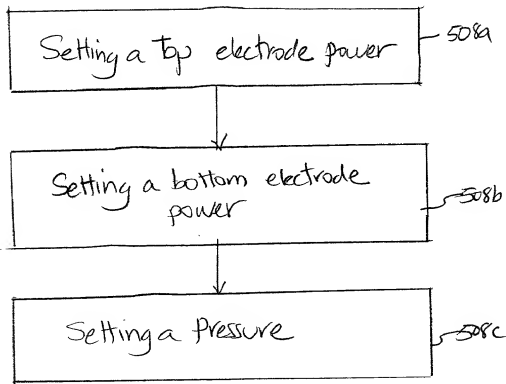


FIG. 5C